



#### TSM210N06CZ C0G Information

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Part Number TSM210N06CZ COG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET, SINGLE, N-CHANNEL, TRENC

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

For Reference Only

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# TSM210N06CZ C0G Specifications

Manufacturer Part Number         TSM210N06CZ COG           Manufacturer         TSC America Inc.           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         210A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         160nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         7900pF @ 30V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         250W (Tc)           Rds On (Max) @ Id, Vgs         3.1 mOhm @ 90A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220           Package / Case         TO-220-3		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package TO-220-3  Series - FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) Rds On (Max) @ 1d, Vgs 3.1 mohm @ 90A, 10V  Operating Temperature  Supplier Device Package Package / Case  TO-220  Package / Case	Manufacturer Part Number	TSM210N06CZ COG
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         210A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         160nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         7900pF @ 30V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         250W (Tc)           Rds On (Max) @ Id, Vgs         3.1 mOhm @ 90A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3	Manufacturer	TSC America Inc.
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C210A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs160nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7900pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs3.1 mOhm @ 90A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  3.1 mOhm @ 90A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  4V @ 250μA  160nC @ 10V  7900pF @ 30V  ±20V  FET Ge 30V  ±20V  FET Feature  -  Through Hole  Through Hole  TO-220-3	Current - Continuous Drain (Id) @ 25°C	210A (Tc)
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Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220  Package / Case  TO-220-3	Power Dissipation (Max)	250W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	3.1 mOhm @ 90A, 10V
Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
		Report errors?

#### TSM210N06CZ C0G Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### TSM210N06CZ C0G Payment Methods





















### TSM210N06CZ COG Shipping Methods













If you have any question about TSM210N06CZ COG, please do not hesitate to contact us!

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